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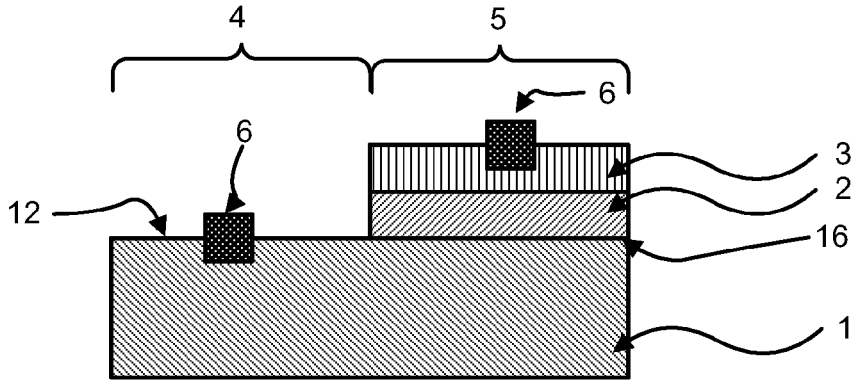


FIG. 3

(57) Abstract: In preferred embodiments, this invention provides a semiconductor structure that has a semi-conducting support, an insulating layer arranged on a portion of the support and a semi-conducting superficial layer arranged on the insulating layer. Electronic devices can be formed in the superficial layer and also in the exposed portion of the semi-conducting bulk region of the substrate not covered by the insulating layer. The invention also provides methods of fabricating such semiconductor structures which, starting from a substrate that includes a semi-conducting superficial layer arranged on a continuous insulating layer both of which being arranged on a semi-conducting support, by transforming at least one selected region of a substrate so as to form an exposed semi-conducting bulk region of the substrate.

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